

**Features:**

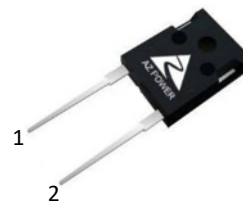
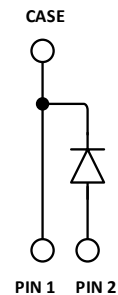
- 1200V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent

## Switching

**Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

| Symbol                            | Value | Unit |
|-----------------------------------|-------|------|
| $V_{RRM}$                         | 1200  | V    |
| $I_F$ ( $T_C=161^\circ\text{C}$ ) | 20    | A    |
| $Q_C$                             | 186   | nC   |

**Outline**

**TO-247-2**
**Circuit**

**Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

**Maximum Ratings**

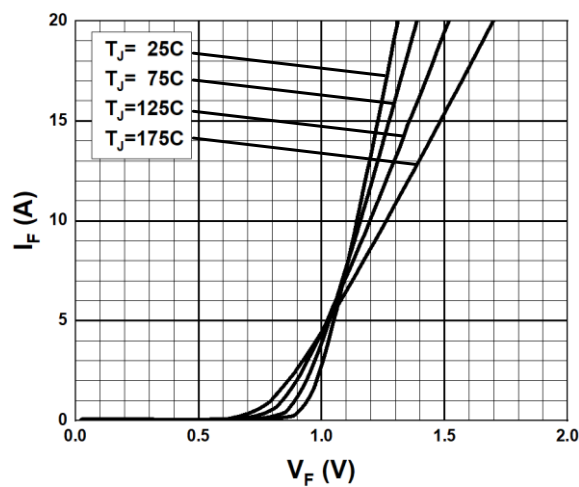
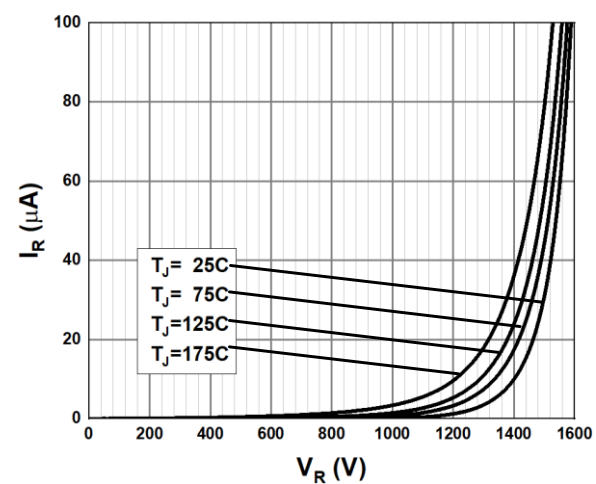
| Symbol      | Parameter                                 | Value      | Unit             | Test Conditions   |
|-------------|---|------------|------------------|---|
| $V_R$       | DC Peak Reverse Voltage                   | 1200       | V                | $T_J=25^\circ\text{C}$  |
| $V_{RRM}$   | Repetitive Peak Reverse Voltage           | 1200       | V                | $T_J=25^\circ\text{C}$  |
| $V_{RSM}$   | Surge Peak Reverse Voltage                | 1300       | V                | $T_J=25^\circ\text{C}$  |
| $I_F$       | Continuous Forward Current                | 85         | A                | $T_C=25^\circ\text{C}$  |
|             |   | 40         |                  | $T_C=135^\circ\text{C}$   |
|             |   | 20         |                  | $T_C=161^\circ\text{C}$   |
| $I_{FRM}$   | Repetitive Peak Forward Surge Current     |            | A                | $T_C=25^\circ\text{C}, T_P=10\text{ms}, \text{Half Sine Wave}$<br>$T_C=125^\circ\text{C}, T_P=10\text{ms}, \text{Half Sine Wave}$ |
| $I_{FSM}$   | Non-Repetitive Peak Forward Surge Current |            | A                | $T_C=25^\circ\text{C}, T_P=10\text{ms}, \text{Half Sine Wave}$<br>$T_C=125^\circ\text{C}, T_P=10\text{ms}, \text{Half Sine Wave}$ |
| $P_D$       | Power Dissipation                         | 395        | W                | $T_C=25^\circ\text{C}$  |
|             |   | 131        |                  | $T_C=125^\circ\text{C}$   |
| $T_{J,max}$ | Operating Junction Temperature            | 175        | $^\circ\text{C}$ |   |
| $T_{stg}$   | Storage Temperature Range                 | -55 to 175 | $^\circ\text{C}$ |   |

**Thermal characteristics**

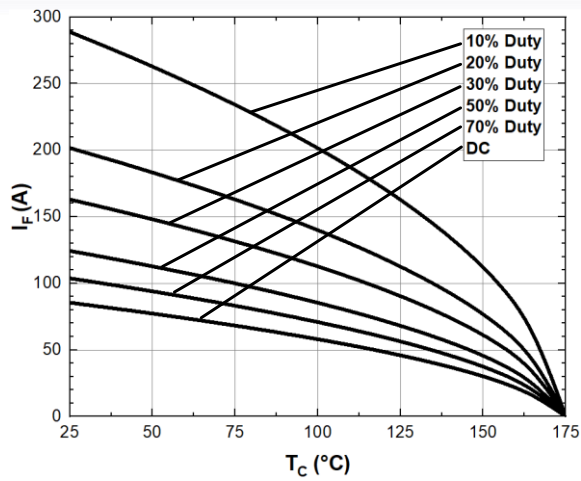
| Symbol     | Parameter          | Min. | Typ. | Max. | Unit                        |
|------------|--------------------|------|------|------|-----------------------------|
| $R_{thJC}$ | Thermal resistance |      | 0.38 |      | $^{\circ}\text{C}/\text{W}$ |

**Electrical Characteristics**

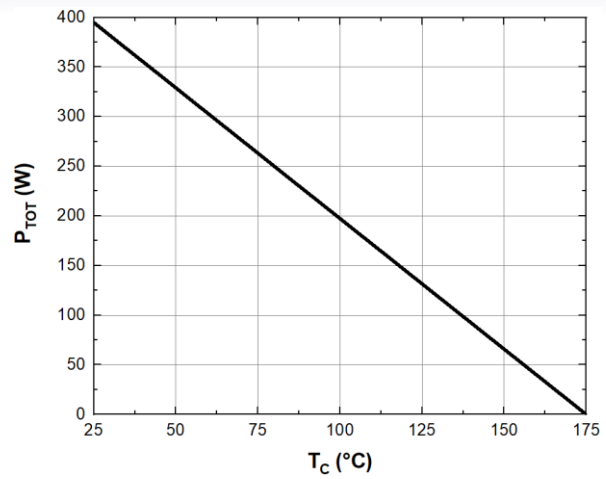
| Symbol   | Parameter               | Value |                    |             | Unit          | Test Conditions   |
|----------|-------------------------|-------|--------------------|-------------|---------------|---|
|          |                         | Min.  | Typ.               | Max.        |               |   |
| $V_{DC}$ | DC Blocking Voltage     | 1200  |                    |             | V             | $I_R=400\mu\text{A}$ , $T_J=25^{\circ}\text{C}$   |
| $V_F$    | Forward Voltage         |       | 1.3<br>1.7         | 1.55<br>2.0 | V             | $I_F=20\text{A}$ , $T_J=25^{\circ}\text{C}$<br>$I_F=20\text{A}$ , $T_J=175^{\circ}\text{C}$   |
| $I_R$    | Reverse Current         |       | 5<br>20            | 100<br>500  | $\mu\text{A}$ | $V_R=1200\text{V}$ , $T_J=25^{\circ}\text{C}$<br>$V_R=1200\text{V}$ , $T_J=175^{\circ}\text{C}$   |
| $Q_C$    | Total Capacitive Charge |       | 186                |             | nC            | $I_F=20\text{A}$ , $di/dt=275\text{A}/\mu\text{s}$<br>$T_J=25^{\circ}\text{C}$ , $V_R=800\text{V}$  |
| C        | Total Capacitance       |       | 1873<br>172<br>148 |             | pF            | $V_R=1\text{V}$ , $T_J=25^{\circ}\text{C}$ , $f=1\text{ MHz}$<br>$V_R=400\text{V}$ , $T_J=25^{\circ}\text{C}$ , $f=1\text{ MHz}$<br>$V_R=800\text{V}$ , $T_J=25^{\circ}\text{C}$ , $f=1\text{ MHz}$ |

**Typical Performance**

**Fig. 1 Forward Characteristics**

**Fig. 2 Reverse Characteristics**

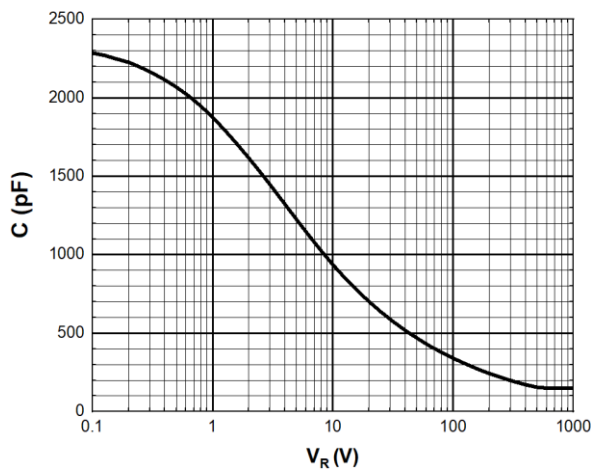
**Typical Performance**



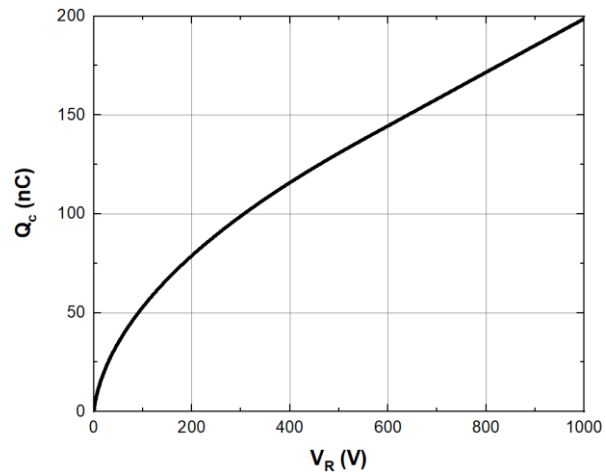
**Fig. 3 Current Derating**



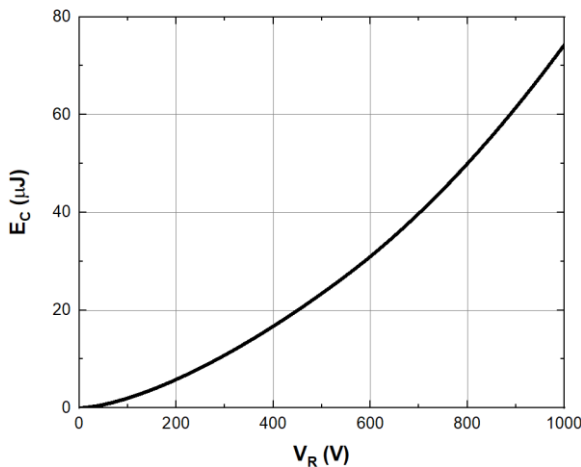
**Fig. 4 Power Derating**



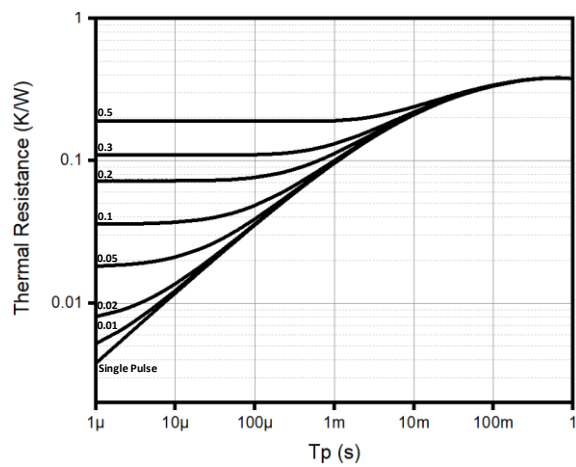
**Fig. 5 Capacitance vs. Reverse Voltage**



**Fig. 6 Recovery Charge vs. Reverse Voltage**



**Fig. 7 Capacitance stored Energy**



**Fig. 8 Transient Thermal Impedance**

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